

FDMC8878

N-Channel POWERTRENCH[®] MOSFET 30 V, 16.5 A, 14 mΩ

This N-Channel MOSFET is a rugged gate version of ON Semiconductor's advanced PowerTrench process. It has been optimized for power management applications.

Features

- $R_{DS(on)} = 14 \text{ m}\Omega$ (Max.) @ $V_{GS} = 10 \text{ V}$, $I_D = 9.6 \text{ A}$
- $R_{DS(on)} = 17 \text{ m}\Omega$ (Max.) @ $V_{GS} = 4.5 \text{ V}$, $I_D = 8.7 \text{ A}$
- Low Profile – 0.8 mm Max in MLP 3.3 x 3.3
- These Devices are Pb-Free and are RoHS Compliant

Application

- DC – DC Conversion

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DS}	30	V
Gate-to-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$T_C = 25^\circ\text{C}$ (Package limited)	I_D	16.5 A
	$T_C = 25^\circ\text{C}$ (Silicon limited)		38
	$T_A = 25^\circ\text{C}$ (Figure 1)		9.6
Drain Current	Pulsed	I_D	60 A
Power Dissipation	$T_C = 25^\circ\text{C}$	P_D	31 W
	$T_A = 25^\circ\text{C}$ (Figure 1)		2.1
Operating and Storage Junction Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	4	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient (Figure 1)	$R_{\theta JA}$	60	

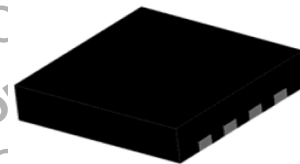
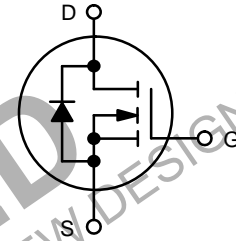
PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Mark	Package	Reel Size	Tape Width	Quantity
FDMC8878	FDMC8878	MLP 3.3 x 3.3	13"	12 mm	3000 units

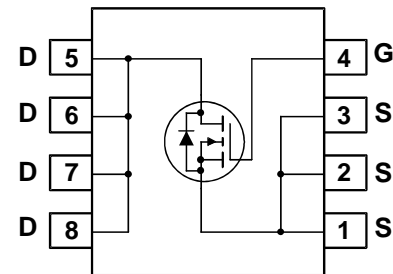


ON Semiconductor[®]

www.onsemi.com



WDFN8
CASE 511DH



ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 1 of this data sheet.

FDMC8878

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
BV_{DSS}	Drain-to-Source Breakdown Voltage	$I_D = 250 \mu\text{A}$, $V_{GS} = 0 \text{ V}$	30	-	-	V
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$, Referenced to 25°C	-	20	-	mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 24 \text{ V}$, $V_{GS} = 0 \text{ V}$	-	-	1	μA
		$V_{DS} = 24 \text{ V}$, $V_{GS} = 0 \text{ V}$, $T_J = 125^\circ\text{C}$	-	-	100	
I_{GSS}	Gate-to-Source Leakage Current	$V_{GS} = \pm 20 \text{ V}$, $V_{DS} = 0 \text{ V}$	-	-	± 100	nA

ON CHARACTERISTICS

$V_{GS(th)}$	Gate-to-Source Breakdown Voltage	$I_D = 250 \mu\text{A}$, $V_{GS} = V_{DS}$	1	1.7	3	V
$\Delta BV_{DSS}/\Delta T_J$	Gate-to-Source Threshold Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$, Referenced to 25°C	-	-5.7	-	mV/ $^\circ\text{C}$
$R_{DS(on)}$	Drain-to-Source On Resistance	$V_{GS} = 10 \text{ V}$, $I_D = 9.6 \text{ A}$	-	9.6	14.0	m Ω
		$V_{GS} = 4.5 \text{ V}$, $I_D = 8.7 \text{ A}$	-	12.1	17.0	
		$V_{GS} = 10 \text{ V}$, $I_D = 9.6 \text{ A}$, $T_J = 125^\circ\text{C}$	-	13.5	20.0	
g_{FS}	Forward Transconductance	$V_{DS} = 5 \text{ V}$, $I_D = 9.6 \text{ A}$	-	35	-	S

DYNAMIC CHARACTERISTICS

C_{iss}	Input Capacitance	$V_{DS} = 15 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 1 \text{ MHz}$	-	1000	1230	pF
C_{oss}	Output Capacitance		-	183	255	pF
C_{rss}	Reverse Transfer Capacitance		-	118	180	pF
R_g	Reverse Transfer Capacitance		$f = 1 \text{ MHz}$	-	1.1	-

SWITCHING CHARACTERISTICS

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 15 \text{ V}$, $I_D = 9.6 \text{ A}$, $V_{GS} = 10 \text{ V}$, $R_{GEN} = 6 \Omega$	-	8	16	ns
t_r	Rise Time		-	4	10	
$t_{d(off)}$	Turn-Off Delay Time		-	20	36	
t_f	Fall Time		-	3	10	
$Q_{g(tot)}$	Total Gate Charge	$V_{GS} = 10 \text{ V}$, $V_{DD} = 15 \text{ V}$, $I_D = 9.6 \text{ A}$	-	18	26	nC
Q_{gs}	Gate-to-Source Gate Charge		-	2.8	-	
Q_{gd}	Gate-to-Drain "Miller" Charge		-	3.9	-	

DRAIN-SOURCE DIODE CHARACTERISTICS

V_{SD}	Source-to-Drain Diode Forward Voltage	$V_{GS} = 0 \text{ V}$, $I_S = 9.6 \text{ A}$ (Note 2)	-	0.8	1.2	V
t_{rr}	Reverse Recovery Time	$I_F = 9.6 \text{ A}$, $di/dt = 100 \text{ A}/\mu\text{s}$	-	23	35	ns
Q_{rr}	Reverse Recovery Charge		-	14	21	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. $R_{\theta JA}$ is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.

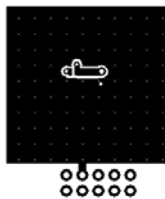


Figure 1.

a. $60^\circ\text{C}/\text{W}$ when mounted on a 1 in² pad of 2 oz copper

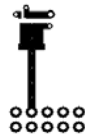


Figure 2.

b. $135^\circ\text{C}/\text{W}$ when mounted on a minimum pad of 2 oz copper

2. Pulse Test: Pulse Width < 300 μs , Duty cycle < 2.0%.

TYPICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

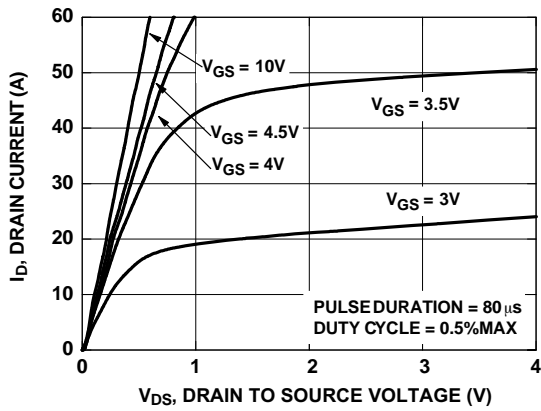


Figure 3. Gate Charge Characteristics

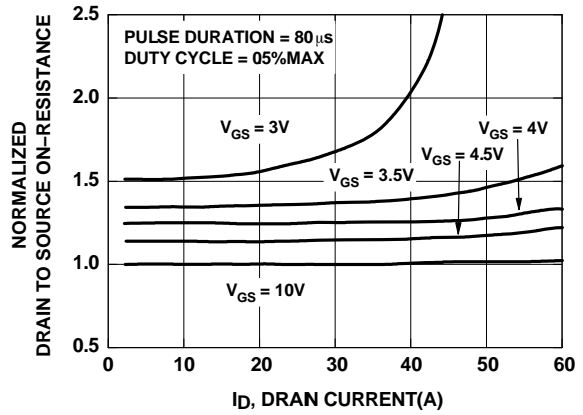


Figure 4. Capacitance vs. Drain to Source Voltage

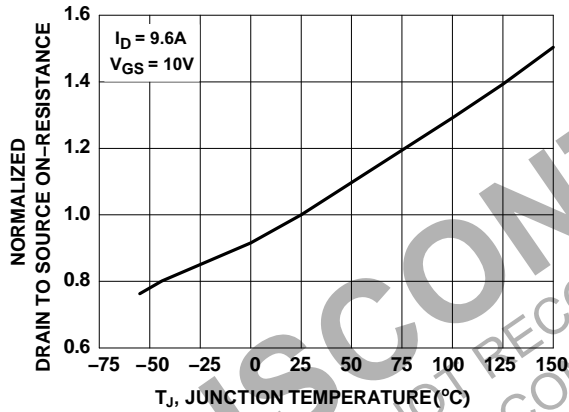


Figure 5. Unclamped Inductive Switching Capability

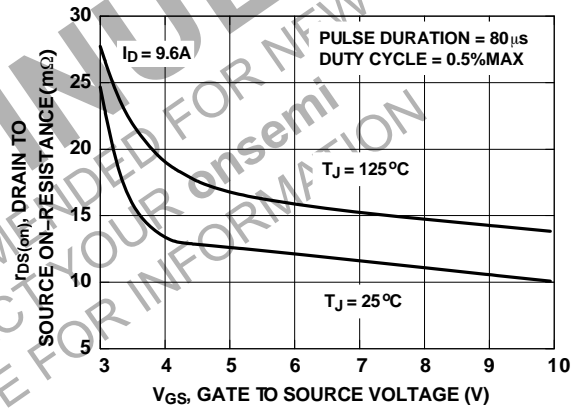


Figure 6. Maximum Continuous Drain Current vs. Ambient Temperature

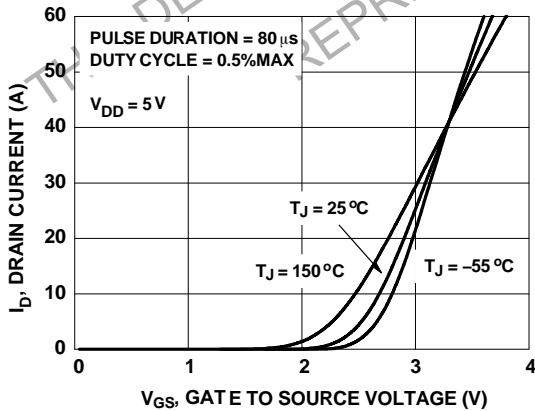


Figure 7. Forward Bias Safe Operating Area

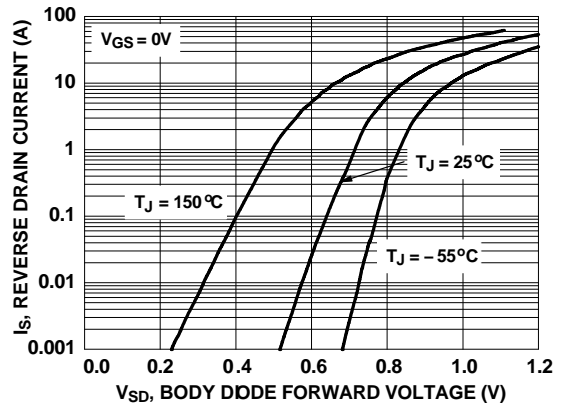


Figure 8. Single Pulse Maximum Power Dissipation

TYPICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

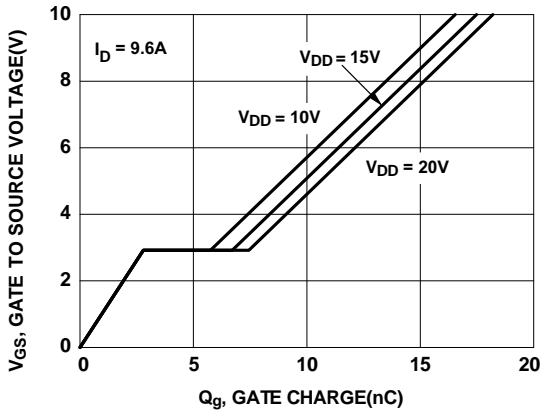


Figure 9. On-Region Characteristics

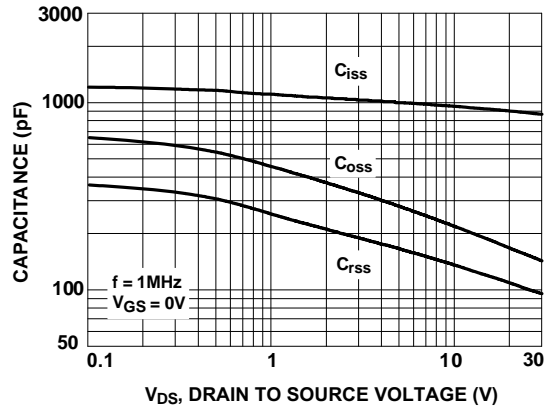


Figure 10. Transfer Characteristics

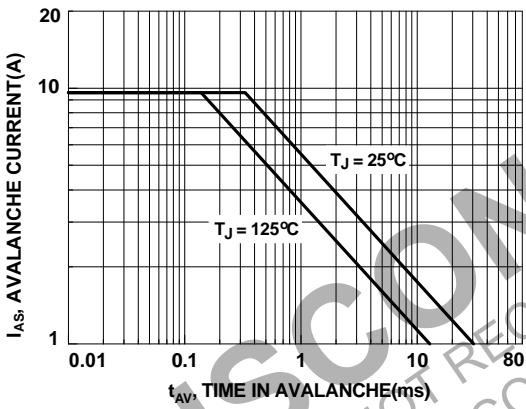


Figure 11. On-Resistance Variation vs. Drain Current and Gate Voltage

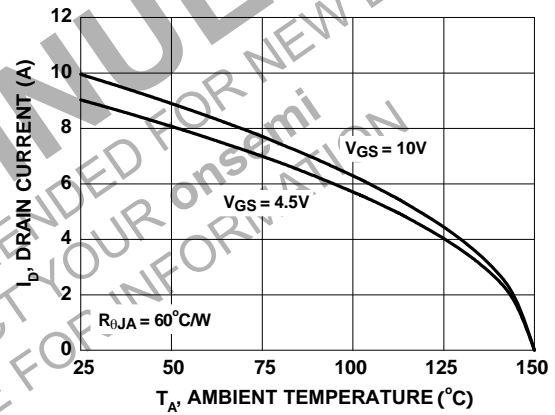


Figure 12. Body Diode Forward Voltage Variation vs. Source Current and Temperature

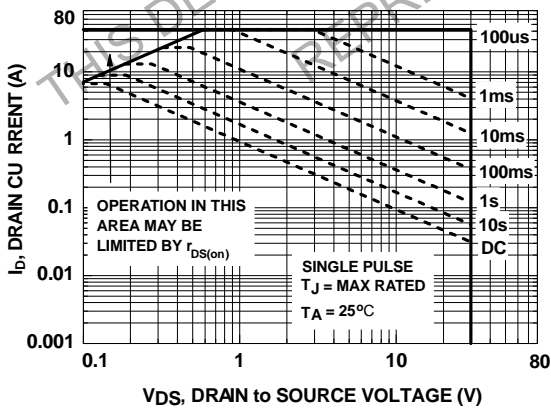


Figure 13. Capacitance Characteristics

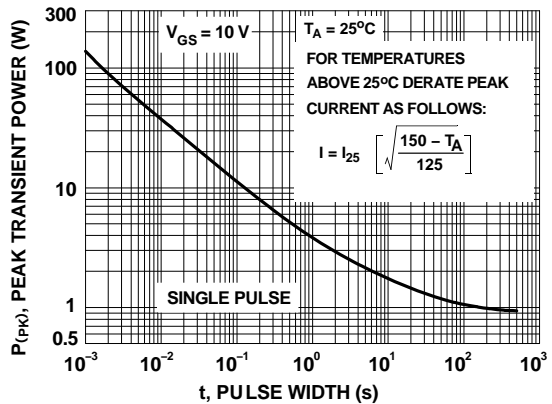


Figure 14. Gate Charge Characteristics

TYPICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

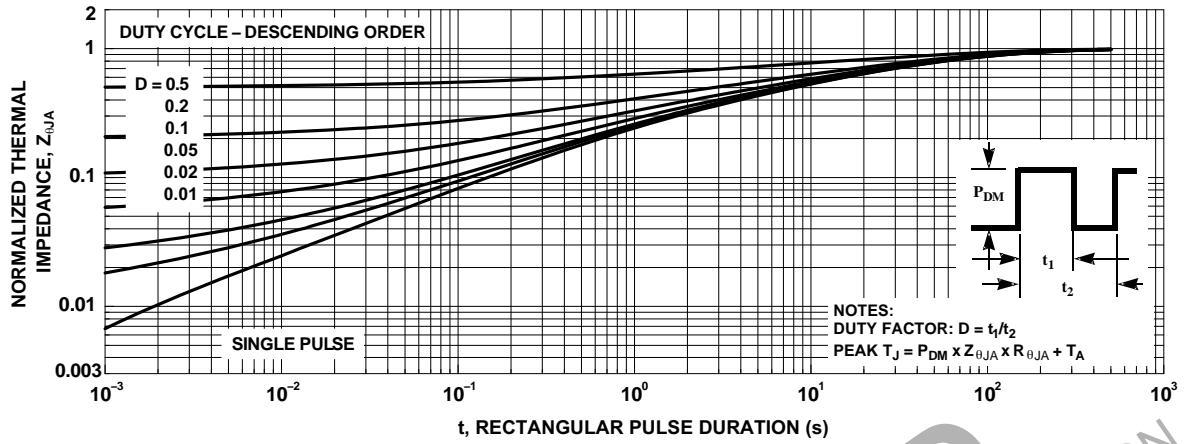
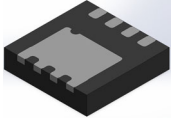


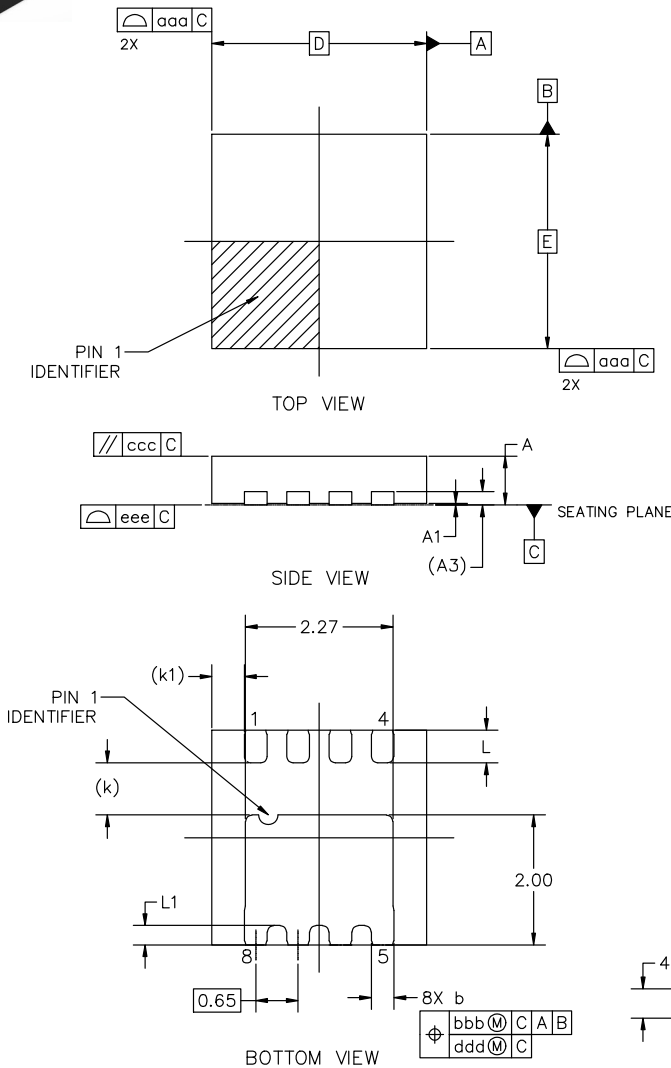
Figure 15. Transient Thermal Response Curve

DISCONTINUED
 THIS DEVICE IS NOT RECOMMENDED FOR NEW DESIGN
 PLEASE CONTACT YOUR onsemi
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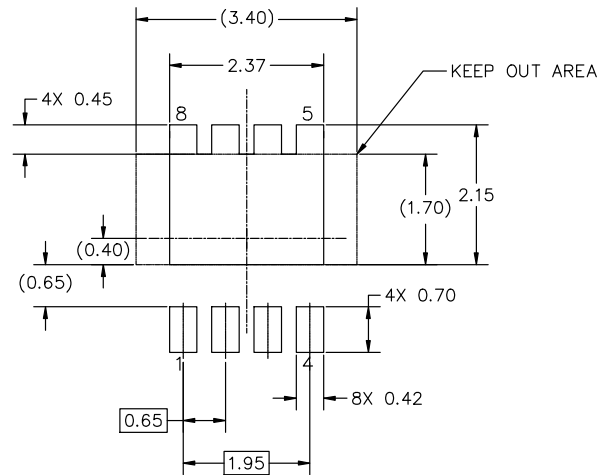
WDFN-8 3.30x3.30x0.75, 0.65P
CASE 511DH
ISSUE A

DATE 04 DEC 2025



- NOTES:
1. DIMENSIONING AND TOLERANCING AS PER ASME Y14.5M, 2018.
 2. CONTROLLING DIMENSION: MILLIMETERS.

MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.70	0.75	0.80
A1	0.00	0.025	0.05
A3	0.20 REF		
b	0.30	0.35	0.40
D	3.30 BSC		
D2	2.22	2.27	2.32
E	3.30 BSC		
E2	1.95	2.00	2.05
e	0.65 BSC		
k	0.80 REF		
k1	0.50 REF		
L	0.45	0.50	0.55
L1	0.25	0.30	0.35
TOLERANCE FORM & POSITION			
aaa	0.05		
bbb	0.10		
ccc	0.10		
ddd	0.05		
eee	0.08		



GENERIC MARKING DIAGRAM*



- XXXX = Specific Device Code
- A = Assembly Location
- Y = Year
- WW = Work Week

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

RECOMMENDED MOUNTING FOOTPRINT
* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques reference manual, SOLDERRM/D.

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DESCRIPTION:	WDFN-8 3.30x3.30x0.75, 0.65P	PAGE 1 OF 1

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